

NST65010MW6

Dual Matched General Purpose Transistor

PNP Matched Pair

These transistors are housed in an ultra-small SOT-363 package ideally suited for portable products. They are assembled to create a pair of devices highly matched in all parameters, eliminating the need for costly trimming. Applications are Current Mirrors; Differential, Sense and Balanced Amplifiers; Mixers; Detectors and Limiters. Complementary NPN equivalent NST65011MW6T1G is available.

Features

- Current Gain Matching to 10%
- Base-Emitter Voltage Matched to ≤ 2 mV
- Drop-In Replacement for Standard Device
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	-65	V
Collector-Base Voltage	V_{CBO}	-80	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-100	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation Per Device FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	380 250	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	328	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-5 = 1.0 x 0.75 x 0.062 in.

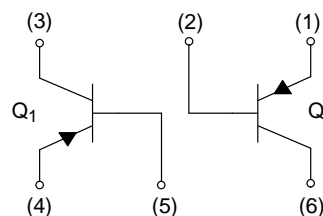


ON Semiconductor®

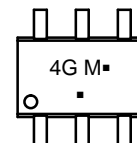
www.onsemi.com



SOT-363
CASE 419B
STYLE 1



MARKING DIAGRAMS



4G = Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NST65010MW6T1G	SOT-363 (Pb-Free)	3000 / Tape & Reel
NSVT65010MW6T1G	SOT-363 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NST65010MW6

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage, (I _C = –10 mA)	V _{(BR)CEO}	–65	–	–	V
Collector–Emitter Breakdown Voltage, (I _C = –10 μA, V _{EB} = 0)	V _{(BR)CES}	–80	–	–	V
Collector–Base Breakdown Voltage, (I _C = –10 μA)	V _{(BR)CBO}	–80	–	–	V
Emitter–Base Breakdown Voltage, (I _E = –1.0 μA)	V _{(BR)EBO}	–5.0	–	–	V
Collector Cutoff Current (V _{CB} = –30 V) (V _{CB} = –30 V, T _A = 150°C)	I _{CBO}	–	–	–15 –5.0	nA μA

ON CHARACTERISTICS

DC Current Gain (I _C = –10 μA, V _{CE} = –5.0 V) (I _C = –2.0 mA, V _{CE} = –5.0 V) (I _C = –2.0 mA, V _{CE} = –5.0 V) (Note 2)	h _{FE} h _{FE(1)} /h _{FE(2)}	– 220 0.9	150 290 1.0	– 475 1.1	–
Collector–Emitter Saturation Voltage (I _C = –10 mA, I _B = –0.5 mA) (I _C = –100 mA, I _B = –5.0 mA)	V _{CE(sat)}	– –	– –	–300 –650	mV
Base–Emitter Saturation Voltage (I _C = –10 mA, I _B = –0.5 mA) (I _C = –100 mA, I _B = –5.0 mA)	V _{BE(sat)}	– –	–700 –900	– –	mV
Base–Emitter On Voltage (I _C = –2.0 mA, V _{CE} = –5.0 V) (I _C = –10 mA, V _{CE} = –5.0 V) (I _C = –2.0 mA, V _{CE} = –5.0 V) (Note 3)	V _{BE(on)} V _{BE(1)} – V _{BE(2)}	–600 – –	– – –1.0	–750 –820 –2.0	mV

SMALL– SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product, (I _C = –10 mA, V _{CE} = –5 Vdc, f = 100 MHz)	f _T	100	–	–	MHz
Output Capacitance, (V _{CB} = –10 V, f = 1.0 MHz)	C _{ob}	–	–	4.5	pF
Noise Figure, (I _C = –0.2 mA, V _{CE} = –5 Vdc, R _S = 2 kΩ, f = 1 kHz, BW = 200Hz)	NF	–	–	10	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- h_{FE(1)}/h_{FE(2)} is the ratio of one transistor compared to the other transistor within the same package. The smaller h_{FE} is used as numerator.
- V_{BE(1)} – V_{BE(2)} is the absolute difference of one transistor compared to the other transistor within the same package.

TYPICAL CHARACTERISTICS

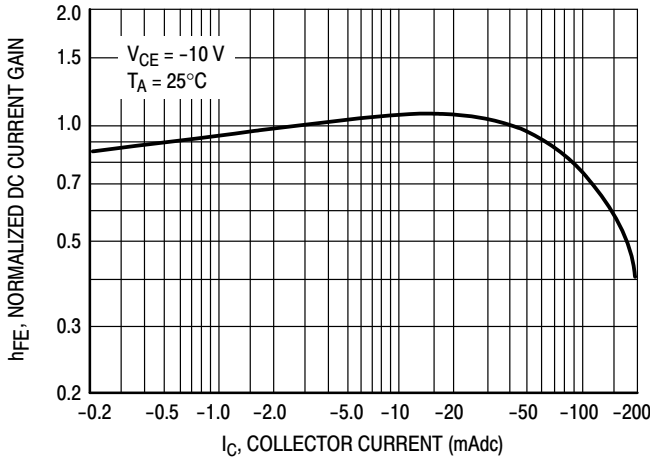


Figure 1. Normalized DC Current Gain

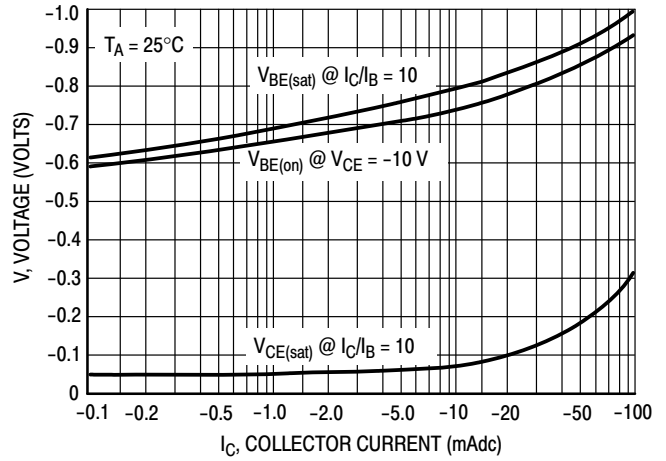


Figure 2. "Saturation" and "On" Voltages

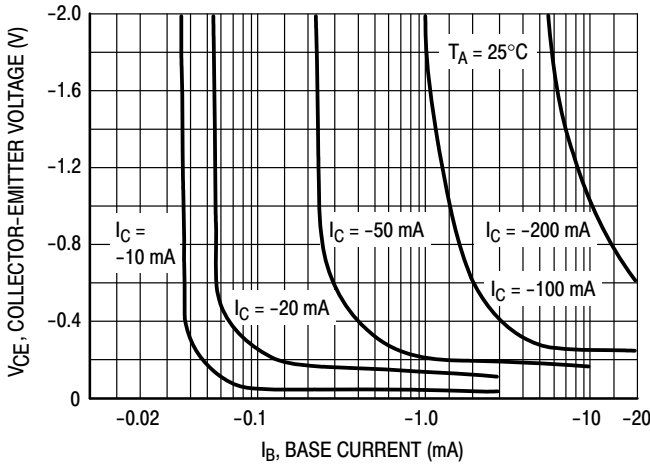


Figure 3. Collector Saturation Region

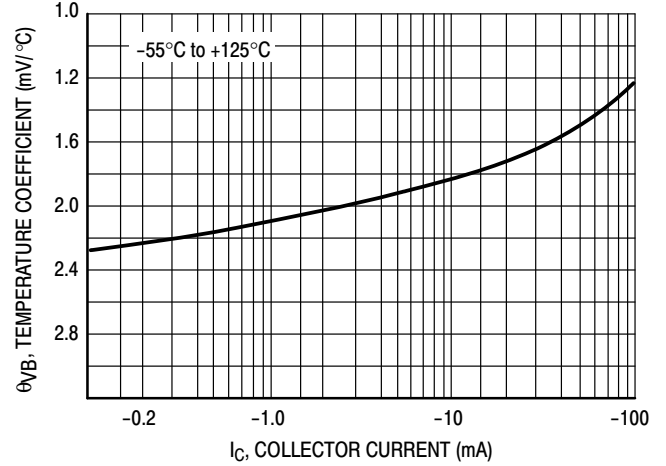


Figure 4. Base-Emitter Temperature Coefficient

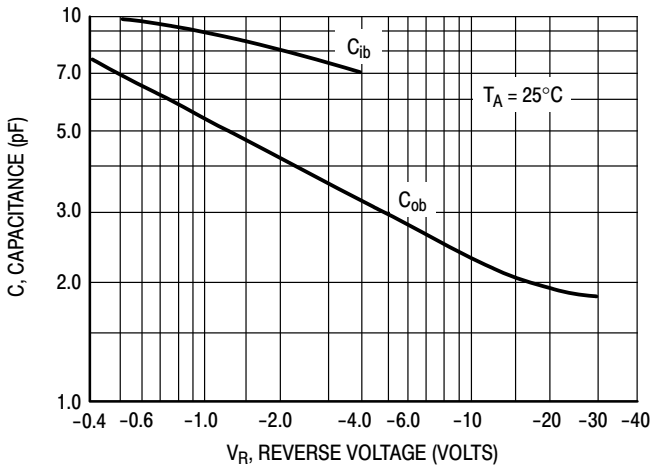


Figure 5. Capacitances

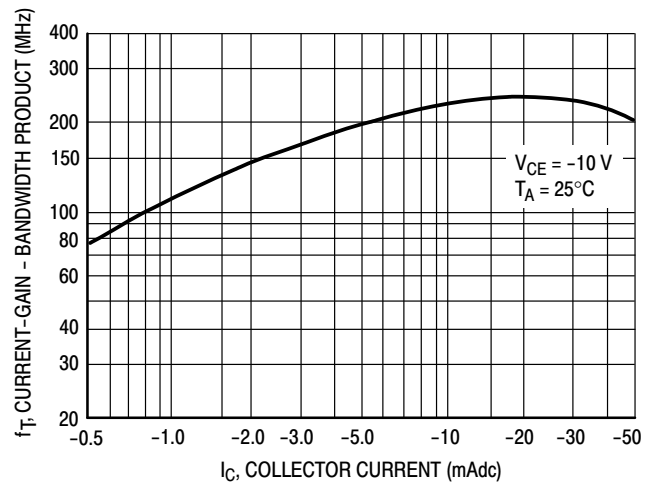


Figure 6. Current-Gain - Bandwidth Product

NST65010MW6

TYPICAL CHARACTERISTICS

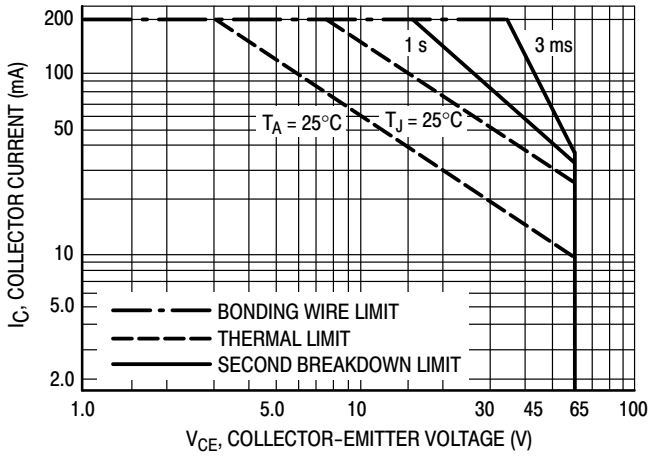


Figure 7. Active Region Safe Operating Area

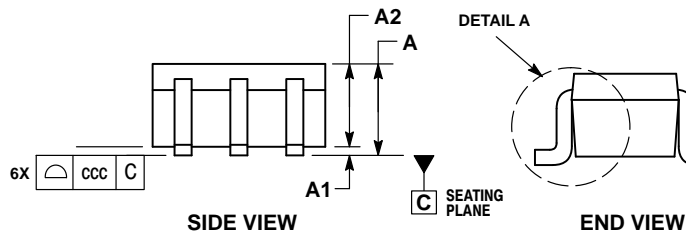
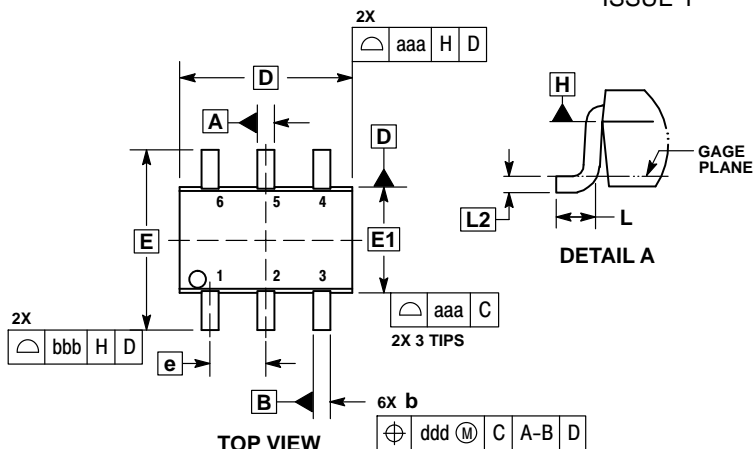
The safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 7 is based upon $T_{J(pk)} = 150^\circ\text{C}$; T_C or T_A is variable depending upon conditions.

NST65010MW6

PACKAGE DIMENSIONS

SC-88 (SOT-363)
CASE 419B-02
ISSUE Y

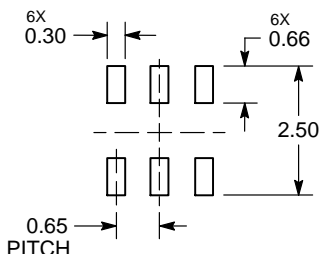


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
 4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
 5. DATUMS A AND B ARE DETERMINED AT DATUM H.
 6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
 7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	0.043
A1	0.00	---	0.10	0.000	---	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		

- STYLE 1:
PIN 1: EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative